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# **BAY72**



#### DO-35 Color Band Denotes Cathode

# **Small Signal Diode**

**Absolute Maximum Ratings\*** 

T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units V	
V <sub>RRM</sub>	Maximum Repetitive Reverse Voltage	125		
I <sub>F(AV)</sub>	Average Rectified Forward Current	200	mA	
I <sub>FSM</sub>	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond	1.0 4.0	A A	
T <sub>stg</sub>	Storage Temperature Range	-65 to +200	°C	
T <sub>1</sub>	Operating Junction Temperature	175	°C	

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES

1) These ratings are based on a maximum junction temperature of 200 degrees C.

### Thermal Characteristics

Symbol	Parameter	Value	Units
P₀	Power Dissipation	500	mW
R <sub>aja</sub>	Thermal Resistance, Junction to Ambient	300	°C/W

# Electrical Characteristics T<sub>x</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
V <sub>R</sub>	Breakdown Voltage	I <sub>R</sub> = 100 μA	125		V
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 1.0 mA   I <sub>F</sub> = 10 mA   I <sub>F</sub> = 50 mA   I <sub>F</sub> = 100 mA	0.51 0.63 0.73 0.78	0.64 0.78 0.92 1.0	V V V
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 100 V V <sub>R</sub> = 100 V, T <sub>Δ</sub> = 125°C		100 100	nA μA
Ст	Total Capacitance	V <sub>R</sub> = 0, f = 1.0 MHz		5	pF
t <sub>m1</sub>	Reverse Recovery Time	I <sub>F</sub> = I <sub>R</sub> = 30 mA, I <sub>rr</sub> = 1.0 mA		50	ns
t <sub>m2</sub>	Reverse Recovery Time	I <sub>F</sub> = 30 mA, V <sub>R</sub> = 35 V		400	ns



<sup>2)</sup> These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.